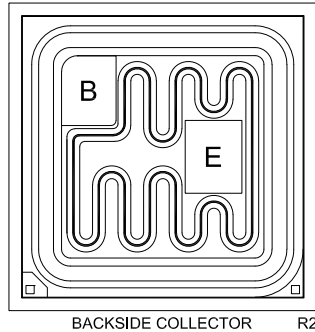


CP591X-2N2907A

PNP - General Purpose Transistor Die

0.6 Amp, 60 Volt

The CP591X-2N2907A is a silicon PNP transistor designed for general purpose applications.



MECHANICAL SPECIFICATIONS:

Die Size	19.3 x 19.3 MILS
Die Thickness	5.9 MILS
Base Bonding Pad Size	3.5 x 4.3 MILS
Emitter Bonding Pad Size	3.5 x 4.5 MILS
Top Side Metalization	Al – 13,000Å
Back Side Metalization	Au – 9,000Å
Scribe Alley Width	1.75 MILS
Wafer Diameter	5 INCHES
Gross Die Per Wafer	45,900

MAXIMUM RATINGS: (T_A=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V _{CB0}	60	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Continuous Collector Current	I _C	600	mA
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C

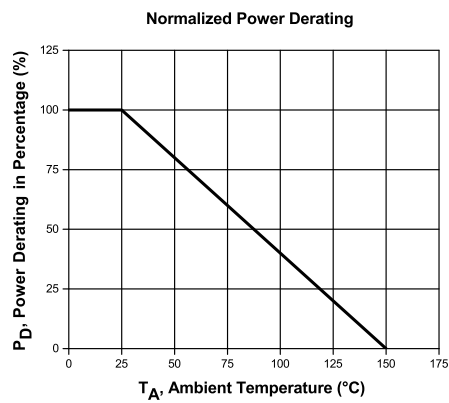
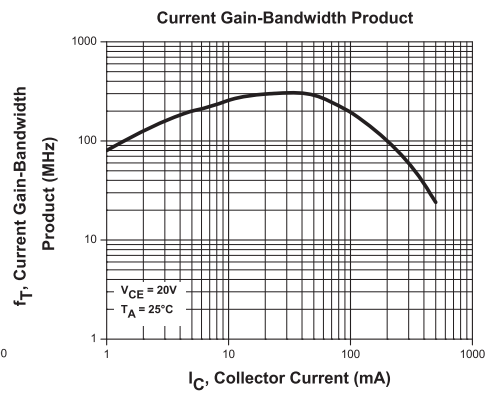
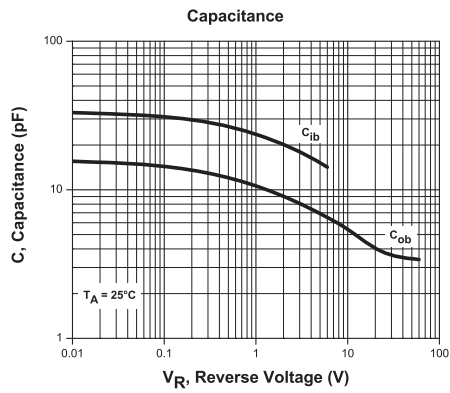
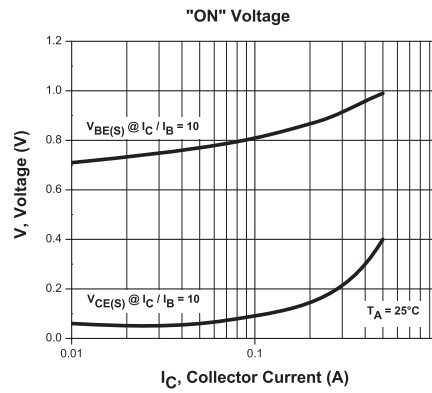
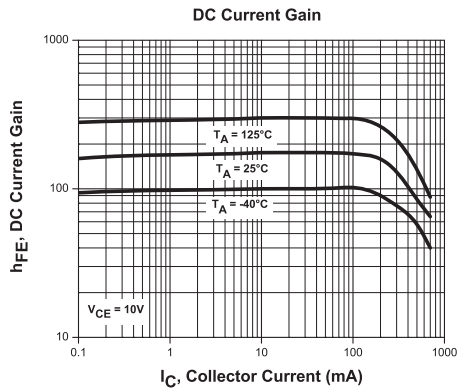
ELECTRICAL CHARACTERISTICS: (T_A=25°C)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CBO}	V _{CB} =50V		10	nA
I _{CEV}	V _{CE} =30V, V _{EB} =0.5V		50	nA
BV _{CB0}	I _C =10μA	60		V
BV _{CEO}	I _C =10mA	60		V
BV _{EBO}	I _E =10μA	5.0		V
V _{CE(SAT)}	I _C =150mA, I _B =15mA		0.4	V
V _{CE(SAT)}	I _C =500mA, I _B =50mA		1.6	V
V _{BE(SAT)}	I _C =150mA, I _B =15mA		1.3	V
V _{BE(SAT)}	I _C =500mA, I _B =50mA		2.6	V
h _{FE}	V _{CE} =10V, I _C =0.1mA	75		
h _{FE}	V _{CE} =10V, I _C =1.0mA	100		
h _{FE}	V _{CE} =10V, I _C =10mA	100		
h _{FE}	V _{CE} =10V, I _C =150mA	100	300	
h _{FE}	V _{CE} =10V, I _C =500mA	50		
f _T	V _{CE} =20V, I _C =50mA, f=100MHz	200		MHz
C _{ob}	V _{CB} =10V, I _E =0, f=1.0MHz		8.0	pF
C _{ib}	V _{EB} =2.0V, I _C =0, f=1.0MHz		30	pF
t _{on}	V _{CC} =30V, I _C =150mA, I _{B1} =15mA		45	ns
t _{off}	V _{CC} =6.0V, I _C =150mA, I _{B1} =I _{B2} =15mA		100	ns

R2 (25-April 2017)

CP591X-2N2907A

Typical Electrical Characteristics



OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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